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Characterization of Plasma-Enhanced CVD Processes

Editors: Gerald Lucovsky, Dale E. Ibbotson and Dennis W. Hess

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MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS VOLUME 165

Characterization of Plasma-Enhanced CVD Processes

Symposium held November 27-28, 1989, Boston,
Massachusetts, U.S.A.

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MATERIALS RESEARCH SOCIETY

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Preface

These proceedings are a refereed collection of the invited and contributed papers presented at the symposium on Characterization of Plasma Enhanced CVD Processes held in Boston, Massachusetts on November 27-28, 1989. The symposium was organized into four sessions: I Diagnostics and Modelling; II PECVD of Silicon Oxides and Nitrides; III Semiconductors; and IV Novel Materials/Applications. There were 12 invited papers, and 24 contributed papers. Thirty-one (31) of these are published in these proceedings.

We would like to thank the Office of Naval Research (George B. Wright) for financial support of the symposium, and Teresa Page for her assistance in preparing the manuscripts for publication.

Gerald Lucovsky
Dale E. Ibbotson
Dennis W. Hess

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